

Monolithic Dual Switching Diode Common Cathode

FEATURES

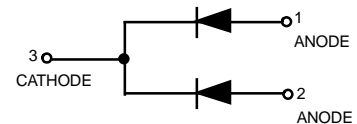
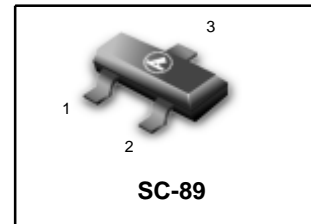
- We declare that the material of product compliance with RoHS requirements.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	555	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate ⁽²⁾ $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.9	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	345	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{slg}	-55 to +150	$^\circ\text{C}$

LBAV70TT1G


ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{Adc}$)	$V_{(BR)}$	70	-	Vdc
Reverse Voltage Leakage Current (3) ($V_R = 70 \text{ Vdc}$) ($V_R = 50 \text{ Vdc}$)	I_R I_R	- -	5.0 100	μAdc nAdc
Diode Capacitance ($V_R = 0, f = 1.0 \text{ MHz}$)	C_D	-	1.5	pF
Forward Voltage ($I_F = 1.0 \text{ mAdc}$) ($I_F = 10 \text{ mAdc}$) ($I_F = 50 \text{ mAdc}$) ($I_F = 150 \text{ mAdc}$)	V_F	- - - -	715 855 1000 1250	mVdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mAdc}, R_L = 100 \Omega, I_{R(REC)} = 1.0 \text{ mAdc}$) (Figure 1)	t_{rr}	-	6.0	ns
Forward Recovery Voltage ($I_F = 10 \text{ mAdc}, t_r = 20 \text{ ns}$) (Figure 2)	V_{RF}	-	1.75	V

1. FR-5 = $1.0 \times 0.75 \times 0.062 \text{ in.}$

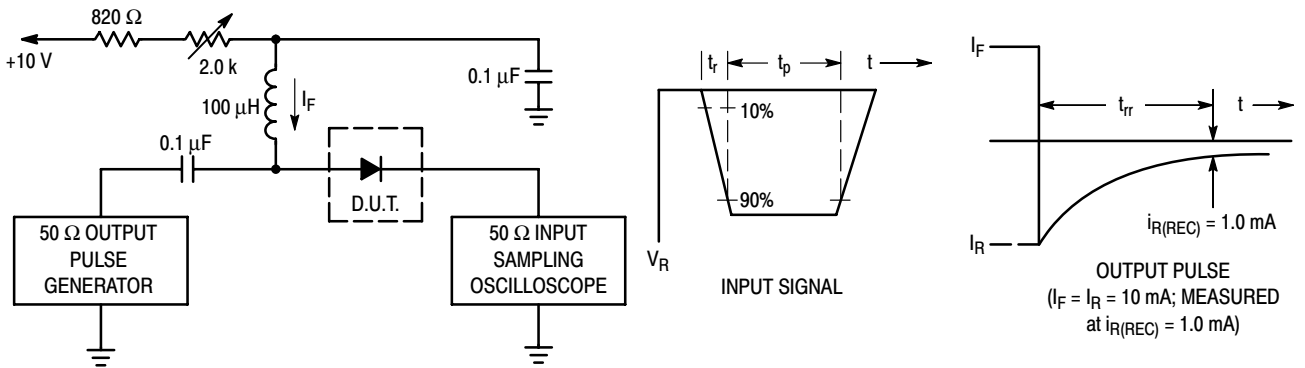
2. Alumina = $0.4 \times 0.3 \times 0.024 \text{ in.}$ 99.5% alumina.

3. For each individual diode while the second diode is unbiased.

ORDERING INFORMATION

Device	Marking	Shipping
LBAV70TT1G	A4	3000 Tape & Reel
LBAV70TT3G	A4	10000 Tape & Reel

LBAV70TT1G



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

Curves Applicable to Each Anode

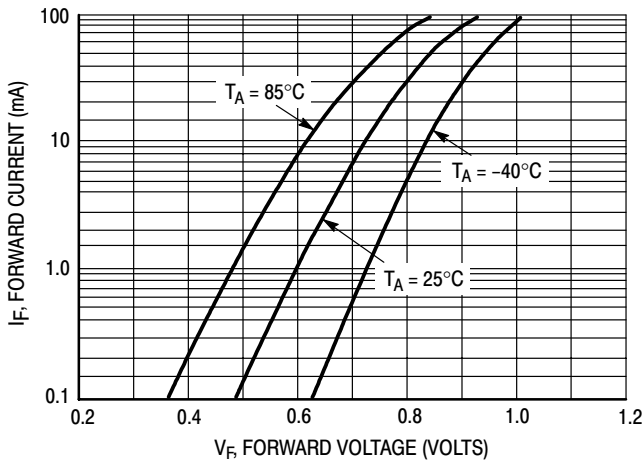


Figure 2. Forward Voltage

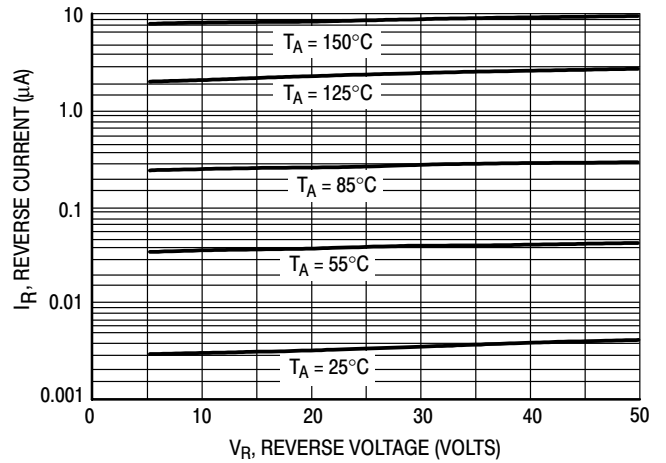


Figure 3. Leakage Current

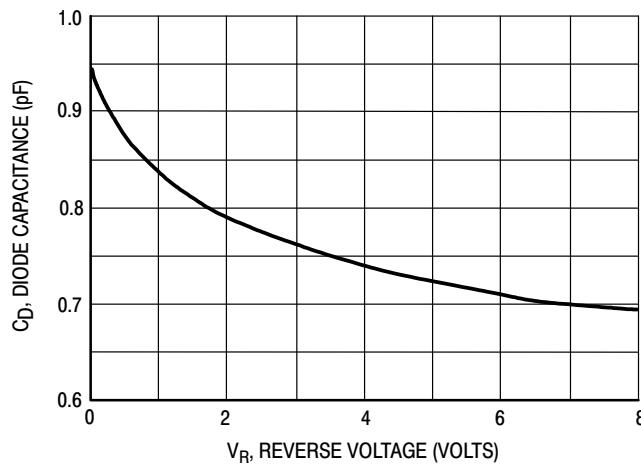
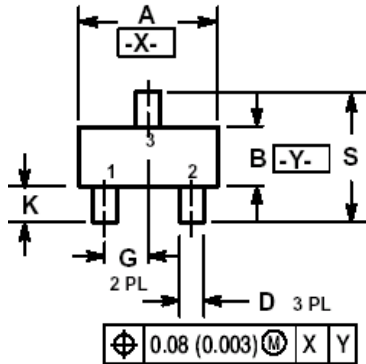
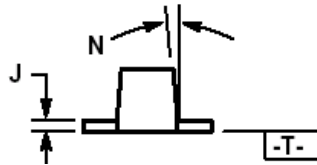
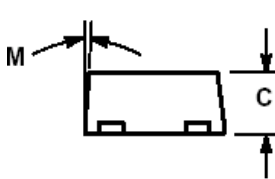


Figure 4. Capacitance

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SC-89


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067

